Dongjin Byun

List of Publications by Year
in descending order

34 papers	669 citations	687363 13 h-index	552781 26 g-index
34 all docs	34 docs citations	34 times ranked	1179 citing authors

#	Article	IF	Citations
1	Inâ€Depth TEM Investigation on Structural Inhomogeneity within a Primary Li_{<i>x</i>}Ni_{0.835}Co_{0.15}Al_{0.015}O₂ Particle: Origin of Capacity Decay during Highâ€Rate Discharge. Angewandte Chemie - International Edition, 2020, 59, 2385-2391.	13.8	16
2	Inâ€Depth TEM Investigation on Structural Inhomogeneity within a Primary Li x Ni 0.835 Co 0.15 Al 0.015 O 2 Particle: Origin of Capacity Decay during Highâ€Rate Discharge. Angewandte Chemie, 2020, 132, 2406-2412.	2.0	4
3	A facile control in freeâ€carbon domain with divinylbenzene for the highâ€rateâ€performing Sb/<scp>SiOC</scp>composite anode material in sodiumâ€ion batteries. International Journal of Energy Research, 2020, 44, 11473-11486.	4.5	15
4	Selective mask formation and gallium nitride template fabrication on patterned sapphire substrates for light-emitting diodes. AIP Advances, 2020, 10, 095001.	1.3	1
5	Passivation effect of zinc oxide thin films with temperature on Si (100) substrate by atomic layer deposition. Phase Transitions, 2020, 93, 407-416.	1.3	0
6	TiNb ₂ O ₇ microsphere anchored by polydopamineâ€modified graphene oxide as a superior anode material in lithiumâ€ion batteries. International Journal of Energy Research, 2020, 44, 4986-4996.	4.5	16
7	Frontispiece: Inâ€Depth TEM Investigation on Structural Inhomogeneity within a Primary Li_{<i>x</i>}Ni_{0.835}Co_{0.15}Al_{0.015}O₂ Particle: Origin of Capacity Decay during Highâ€Rate Discharge. Angewandte Chemie - International Edition, 2020, 59, .	13.8	0
8	Frontispiz: Inâ€Depth TEM Investigation on Structural Inhomogeneity within a Primary Li_{<i>x</i>}Ni_{0.835}Co_{0.15}Al_{0.015}O₂ Particle: Origin of Capacity Decay during Highâ€Rate Discharge. Angewandte Chemie, 2020, 132, .	2.0	0
9	Selective TiO₂ Nanolayer Coating by Polydopamine Modification for Highly Stable Niâ€Rich Layered Oxides. ChemSusChem, 2019, 12, 5253-5264.	6.8	47
10	Polydopamine-derived N-doped carbon-wrapped Na3V2(PO4)3 cathode with superior rate capability and cycling stability for sodium-ion batteries. Nano Research, 2019, 12, 397-404.	10.4	71
11	Highly Secure Plasmonic Encryption Keys Combined with Upconversion Luminescence Nanocrystals. Advanced Functional Materials, 2018, 28, 1800369.	14.9	28
12	Coaxial-nanostructured MnFe₂O₄ nanoparticles on polydopamine-coated MWCNT for anode materials in rechargeable batteries. Nanoscale, 2018, 10, 18949-18960.	5.6	31
13	Effect of Al composition and V/III ratio of AlGaN on GaN for distributed Bragg reflector. Journal of the Korean Physical Society, 2017, 71, 345-348.	0.7	1
14	A nano-LiNbO₃ coating layer and diffusion-induced surface control towards high-performance 5ÂV spinel cathodes for rechargeable batteries. Journal of Materials Chemistry A, 2017, 5, 25077-25089.	10.3	67
15	Effect of Amorphous and Crystalline AlN Buffer Layers Deposited on Patterned Sapphire Substrate on GaN Film Quality. Journal of Nanoscience and Nanotechnology, 2016, 16, 11563-11568.	0.9	7
16	Improvement of Epitaxial GaN Films Grown on Patterned Sapphire Substrate by Growth Mode Control. Journal of Nanoscience and Nanotechnology, 2016, 16, 11575-11579.	0.9	5
17	Plasmonic Nanowireâ€Enhanced Upconversion Luminescence for Anticounterfeit Devices. Advanced Functional Materials, 2016, 26, 7836-7846.	14.9	70
18	A green recycling process designed for LiFePO₄ cathode materials for Li-ion batteries. Journal of Materials Chemistry A, 2015, 3, 11493-11502.	10.3	97

#	Article	IF	Citations
19	Bipolar Switching Behavior of ZnO x Thin Films Deposited by Metalorganic Chemical Vapor Deposition at Various Growth Temperatures. Journal of Electronic Materials, 2015, 44, 4175-4181.	2.2	6
20	Anti-fluorite Li₆CoO₄as an alternative lithium source for lithium ion capacitors: an experimental and first principles study. Journal of Materials Chemistry A, 2015, 3, 12377-12385.	10.3	72
21	Growth and characterization of a multi-dimensional ZnO hybrid structure on a glass substrate by using metal organic chemical vapor deposition. Journal of the Korean Physical Society, 2014, 64, 1524-1528.	0.7	4
22	Mechanochemical Synthesis of Li2MnO3 Shell/LiMO2 (M = Ni, Co, Mn) Core-Structured Nanocomposites for Lithium-Ion Batteries. Scientific Reports, 2014, 4, 4847.	3.3	47
23	Effect of the growth temperature on the properties of AlxGalâˆ’xN epilayers grown by HVPE. Journal of Crystal Growth, 2012, 346, 83-88.	1.5	7
24	Effects of temperature on ZnO hybrids grown by metal-organic chemical vapor deposition. Materials Research Bulletin, 2012, 47, 2888-2890.	5.2	7
25	Effect of deposition temperature and thermal annealing on the dry etch rate of a-C: H films for the dry etch hard process of semiconductor devices. Thin Solid Films, 2012, 520, 5284-5288.	1.8	6
26	Study ofa-Plane GaN Epitaxial Lateral Overgrowth Using Carbonized Photoresist Mask onr-Plane Sapphire. Japanese Journal of Applied Physics, 2012, 51, 115501.	1.5	0
27	Epitaxial lateral overgrowth of GaN on sapphire substrates using in-situ carbonized photoresist mask. Journal of Crystal Growth, 2011, 326, 200-204.	1.5	10
28	Epitaxial Lateral Overgrowth of GaN on Si (111) Substrates Using Highâ€Dose, N⁺ Ion Implantation. Chemical Vapor Deposition, 2010, 16, 80-84.	1.3	13
29	Copper thin films on PET prepared at ambient temperature by ECR-CVD. IEEE Transactions on Components and Packaging Technologies, 2005, 28, 781-784.	1.3	6
30	Effects of Process Parameters on the Adhesion of Copper Film on Polyethylene Tetrephthalate(Pet) Substrate Prepared by ECRMOCVD Coupled with a Periodic DC Bias. Materials Research Society Symposia Proceedings, 2003, 795, 511.	0.1	0
31	The effect of substrate surface roughness on GaN growth using MOCVD process. Journal of Electronic Materials, 1997, 26, 1098-1102.	2.2	15
32	Improved crystalline quality of GaN by substrate ion beam pre-treatment. , 0, , .		0
33	Implantation of N-ion on sapphire substrate for GaN epilayer. , 0, , .		0
34	Influence of intentionally strained sapphire substrate on GaN epilayers. , 0, , .		0